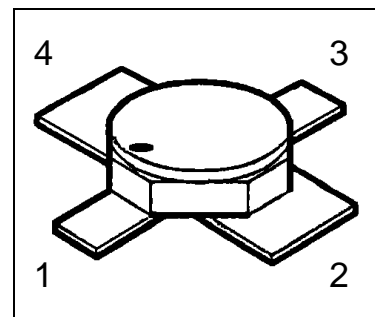


# HiRel NPN Silicon RF Transistor

## BFY650B-12(ES)

### Features

- For high power amplifiers
- Ideal for low phase noise oscillators
- Maximum available gain:  $G_{ma} = 18$  dB at 1.8 GHz  
Noise figure  $F = 0.8$  dB at 1.8 GHz
- Hermetically sealed microwave package



### Product validation

-  **ESA Space Qualified**  
ESCC Detail Spec. No.: 5611/010  
Type Variant No. 05

### Description

**ESD:** Electrostatic discharge sensitive device,  
observe handling precautions!

**Table 1**      **Product information**

Type	Comment	Pin Configuration				Package
		1	2	3	4	
BFY650B-12(ES)	For flight use	C	E	B	E	Micro-X
BFY650B-12(P) <sup>1</sup>	Not for flight use <sup>1</sup>					

<sup>1</sup> (P) parts have the same fit, form and function as (ES) parts,  
no screening acc. to Chart F3 in ESCC Generic Specification No. 5010

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## Maximum ratings

# 1 Maximum ratings

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Collector-emitter voltage	$V_{CEO}$	-	-	4 3.7	V	$T_A > 0\text{ °C}$ $T_A \leq 0\text{ °C}$
Collector-base voltage	$V_{CBO}$	-	-	13	V	
Emitter-base voltage	$V_{EBO}$	-	-	1.2	V	
Collector current	$I_C$	-	-	150	mA	
Base current <sup>1</sup>	$I_B$	-	-	10	mA	
Total power dissipation <sup>2</sup>	$P_{tot}$	-	-	600	mW	$T_s \leq 76\text{ °C}$
Junction temperature	$T_j$	-	-	175	°C	
Operating temperature	$T_{op}$	-65	-	175	°C	
Storage temperature	$T_{stg}$	-65	-	175	°C	

<sup>1</sup> Maximum ratings must not be exceeded under any combination of DC ratings and RF voltage/current swings except as specified in §3

<sup>2</sup> For  $T_s > 76\text{ °C}$  derating is required.  $T_s$  is measured on the collector lead at the soldering point to the PCB

Thermal characteristics

## 2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction –soldering point	$R_{th,JS}$	-	-	165	K/W	$T_s$ is measured on the collector lead at the soldering point to the PCB
Soldering Temperature	$T_{sol}$	-	-	250	°C	Duration 5 seconds maximum at a distance of not less than 0.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

Electrical characteristics

### 3 Electrical characteristics

at  $T_A=25^\circ\text{C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Collector emitter leakage current	$I_{CES}$	-	-	10	$\mu\text{A}$	$V_{CEB} = 13\text{V}$ , E-B short circuited
Collector emitter leakage current	$I_{CES}$	-	-	5	$\mu\text{A}$	$V_{CEB} = 10.5\text{V}$ , E-B short circuited
Collector emitter leakage current	$I_{CES}$	-	-	2	$\mu\text{A}$	$V_{CEB} = 5\text{V}$ , E-B short circuited
Collector-emitter cutoff current <sup>1</sup>	$I_{CEX}$	-	-	160	$\mu\text{A}$	$V_{CE} = 4\text{V}$ , $I_B = 0.1\mu\text{A}$
Emitter base cutoff current	$I_{EBO}$	-	-	15	$\mu\text{A}$	$V_{EB} = 1.2\text{V}$ , $I_C = 0\text{A}$
DC current gain	$h_{FE}$	100	190	250	-	$I_C = 80\text{mA}$ , $V_{CE} = 3\text{V}$

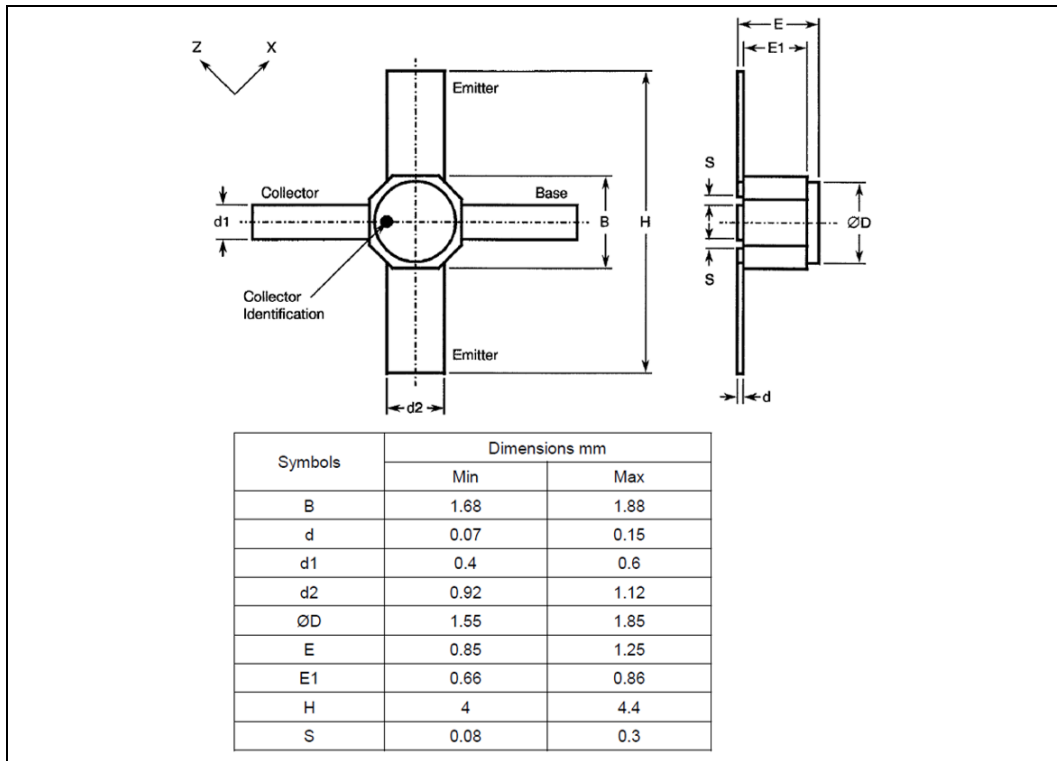
**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Collector-base capacitance	$C_{CB}$	-	0.26	0.36	pF	$V_{CB} = 2\text{V}$ , $V_{BE} = v_{be} = 0$ , $f = 1\text{MHz}$
Collector-emitter capacitance	$C_{CE}$	-	0.57	0.8	pF	$V_{CE} = 2\text{V}$ , $V_{BE} = v_{be} = 0$ , $f = 1\text{MHz}$
Emitter-base capacitance	$C_{EB}$	-	1.4	1.8	pF	$V_{EB} = 0.5\text{V}$ , $V_{CB} = v_{cb} = 0$ , $f = 1\text{MHz}$
Noise Figure	$F$	-	0.8	-	dB	$I_C = 10\text{mA}$ , $V_{CE} = 3\text{V}$ , $f = 1.8\text{GHz}$ , $Z_S = Z_{Sopt}$ $I_C = 10\text{mA}$ , $V_{CE} = 3\text{V}$ , $f = 6.0\text{GHz}$ , $Z_S = Z_{Sopt}$
Insertion power gain	$ S_{21e} ^2$	14.5	18	-	dB	$I_C = 80\text{mA}$ , $V_{CE} = 3\text{V}$ , $f = 1.8\text{GHz}$ , $Z_S = Z_L = 50\Omega$ $I_C = 80\text{mA}$ , $V_{CE} = 3\text{V}$ , $f = 6.0\text{GHz}$ , $Z_S = Z_L = 50\Omega$
Power Gain <sup>2</sup>	$G_{ms}$	18	19.2	-	dB	$I_C = 80\text{mA}$ , $V_{CE} = 3\text{V}$ , $f = 1.8\text{GHz}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$
Power Gain <sup>2</sup>	$G_{ma}$	8	9.3	-	dB	$I_C = 80\text{mA}$ , $V_{CE} = 3\text{V}$ , $f = 6.0\text{GHz}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$
Output Power	$P_{out}$	16		-	dBm	$I_C = 80\text{mA}$ , $V_{CE} = 3\text{V}$ , $f = 1.8\text{GHz}$ , $P_{in} = 0\text{dBm}$

<sup>1</sup> This test assures  $V_{(BR)CE0} > 4\text{V}$

$$^2 G_{ma} = \left| \frac{S_{21}}{S_{12}} \right| (k - \sqrt{k^2 - 1}), G_{ms} = \left| \frac{S_{21}}{S_{12}} \right|$$

## 4 Package outlines



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